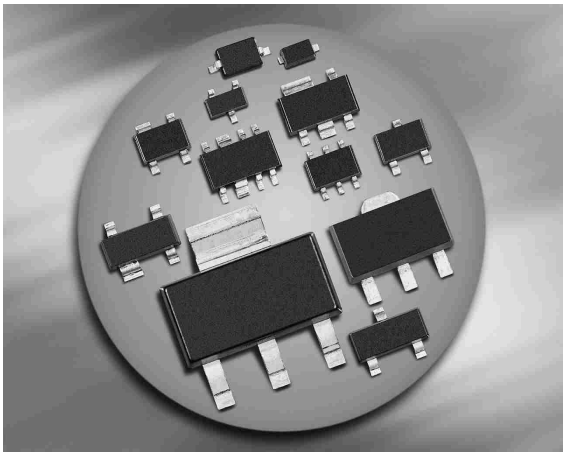
PNP Silicon AF Transistor

- For AF input stages and driver applications
- High current gain
- Low collector-emitter saturation voltage
- Low noise between 30 hz and 15 kHz
- Complementary types:
  BC847...-BC850... (NPN)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101[1)]



AEC Qualified RoHS

[1]BC857BL3 is not qualified according AEC Q101

Type	Marking	Pin Configuration						Package
BC857A	3Es	1=B	2=E	3=C	-	-	-	SOT23
BC857B	3Fs	1=B	2=E	3=C	-	-	-	SOT23
BC857BL3*	3F	1=B	2=E	3=C	-	-	-	TSLP-3-1
BC857BW	3Fs	1=B	2=E	3=C	-	-	-	SOT323
BC857C	3Gs	1=B	2=E	3=C	-	-	-	SOT23
BC857CW	3Gs	1=B	2=E	3=C	-	-	-	SOT323
BC858A	3Js	1=B	2=E	3=C	-	-	-	SOT23
BC858B	3Ks	1=B	2=E	3=C	-	-	-	SOT23
BC858BW	3Ks	1=B	2=E	3=C	-	-	-	SOT323
BC858C	3Ls	1=B	2=E	3=C	-	-	-	SOT23
BC858CW	3Ls	1=B	2=E	3=C	-	-	-	SOT323
BC859C	4Cs	1=B	2=E	3=C	-	-	-	SOT23
BC860B	4Fs	1=B	2=E	3=C	-	-	-	SOT23
BC860BW	4Fs	1=B	2=E	3=C	-	-	-	SOT323
BC860CW	4Gs	1=B	2=E	3=C	-	-	-	SOT323

* Not qualified according AEC Q101

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
BC857..., BC860...		45	
BC858..., BC859...		30	
Collector-base voltage	V_{CBO}		
BC857..., BC860...		50	
BC858..., BC859...		30	
Emitter-base voltage	V_{EBO}	5	
Collector current	I_C	100	mA
Peak collector current, $t_p \leq 10$ ms	I_{CM}	200	
Total power dissipation	P_{tot}		mW
$T_S \leq 71$ °C, BC857-BC860		330	
$T_S \leq 135$ °C, BC857BL3		250	
$T_S \leq 124$ °C, BC857W-BC860W		250	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}		K/W
BC857-BC860		≤ 240	
BC857BL3		≤ 60	
BC857W-BC860W		≤ 105	

[1]For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	$V_{(BR)CEO}$				V
I_C = 10 mA, I_B = 0 , BC857..., BC860...		45	-	-	
I_C = 10 mA, I_B = 0 , BC858..., BC859...		30	-	-	
Collector-base breakdown voltage	$V_{(BR)CBO}$				
I_C = 10 µA, I_E = 0 , BC857..., BC860...		50	-	-	
I_C = 10 µA, I_E = 0 , BC858..., BC859...		30	-	-	
Emitter-base breakdown voltage	$V_{(BR)EBO}$	5	-	-	
I_E = 1 µA, I_C = 0					
Collector-base cutoff current	I_{CBO}				µA
V_{CB} = 45 V, I_E = 0		-	-	0.015	
V_{CB} = 30 V, I_E = 0 , T_A = 150 °C		-	-	5	
DC current gain[1)]	h_{FE}				-
I_C = 10 µA, V_{CE} = 5 V, h_{FE}-grp.A		-	140	-	
I_C = 10 µA, V_{CE} = 5 V, h_{FE}-grp.B		-	250	-	
I_C = 10 µA, V_{CE} = 5 V, h_{FE}-grp.C		-	480	-	
I_C = 2 mA, V_{CE} = 5 V, h_{FE}-grp.A		125	180	250	
I_C = 2 mA, V_{CE} = 5 V, h_{FE}-grp.B		220	290	475	
I_C = 2 mA, V_{CE} = 5 V, h_{FE}-grp.C		420	520	800	
Collector-emitter saturation voltage[1)]	V_{CEsat}				mV
I_C = 10 mA, I_B = 0.5 mA		-	75	300	
I_C = 100 mA, I_B = 5 mA		-	250	650	
Base emitter saturation voltage[1)]	V_{BEsat}				
I_C = 10 mA, I_B = 0.5 mA		-	700	-	
I_C = 100 mA, I_B = 5 mA		-	850	-	
Base-emitter voltage[1)]	$V_{BE(ON)}$				
I_C = 2 mA, V_{CE} = 5 V		600	650	750	
I_C = 10 mA, V_{CE} = 5 V		-	-	820	

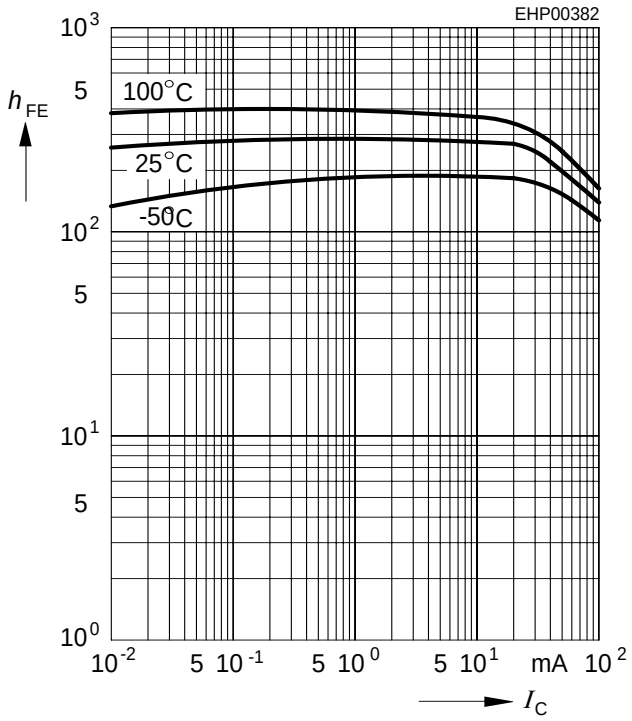
[1]Pulse test: t < 300µs; D < 2%

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency I_C = 20 mA, V_{CE} = 5 V, f = 100 MHz	f_T	-	250	-	MHz
Collector-base capacitance V_{CB} = 10 V, f = 1 MHz	C_{cb}	-	1.5	-	pF
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz	C_{eb}	-	8	-	
Short-circuit input impedance	h_{11e}				kΩ
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	2.7	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	4.5	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	8.7	-	
Open-circuit reverse voltage transf. ratio	h_{12e}				10^{-4}
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	1.5	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	2	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	3	-	
Short-circuit forward current transf. ratio	h_{21e}				-
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	200	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	330	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	600	-	
Open-circuit output admittance	h_{22e}				µS
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.A		-	18	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.B		-	30	-	
I_C = 2 mA, V_{CE} = 5 V, f = 1 kHz, h_{FE}-grp.C		-	60	-	
Noise figure I_C = 0.2 mA, V_{CE} = 5 V, f = 1 kHz, Δf = 200 Hz, R_S = 2 kΩ, BC859, BC850	F	-	1	4	dB
Equivalent noise voltage I_C = 200 mA, V_{CE} = 5 V, R_S = 2 kΩ, f = 10...50 Hz, BC860	V_n	-	-	0.11	µV

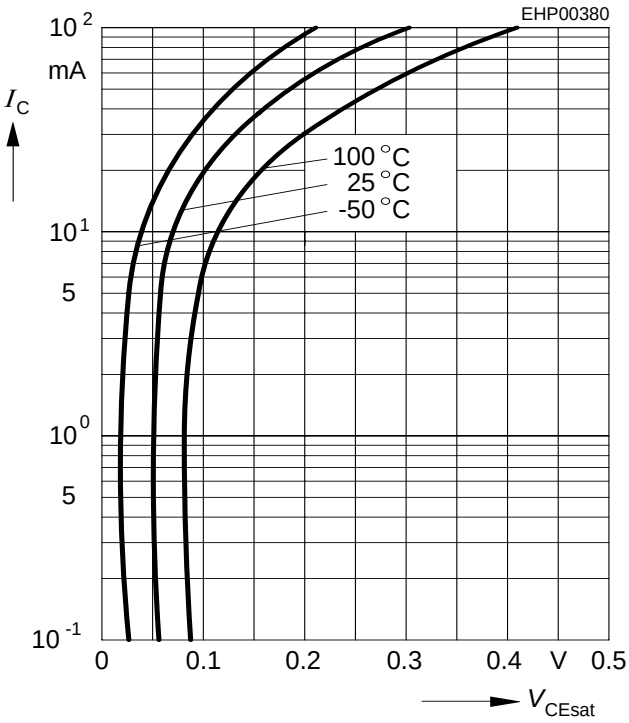
DC current gain $h_{FE} = f(I_C)$

V_{CE} = 1 V



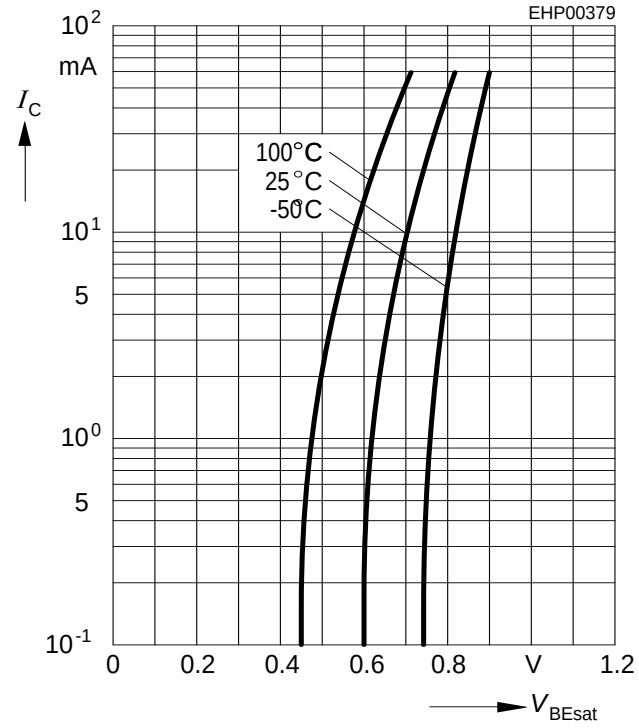
Collector-emitter saturation voltage

$I_C = f(V_{CEsat})$, h_{FE} = 20



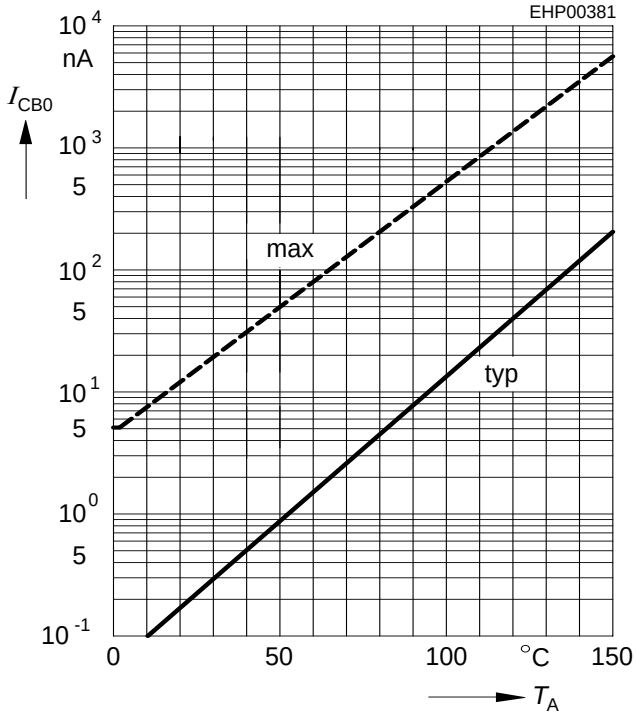
Base-emitter saturation voltage

$I_C = f(V_{BEsat})$, h_{FE} = 20



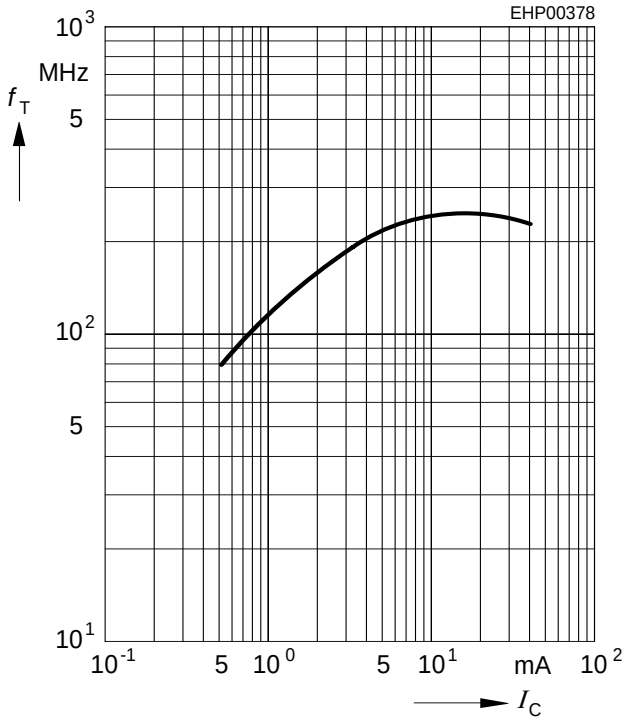
Collector cutoff current $I_{CBO} = f(T_A)$

V_{CBO} = 30 V



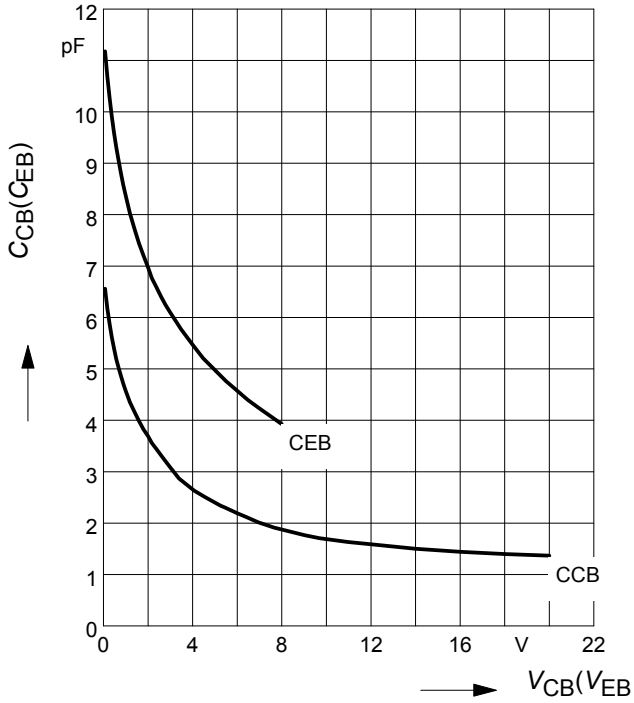
Transition frequency $f_T = f(I_C)$

V_{CE} = 5 V



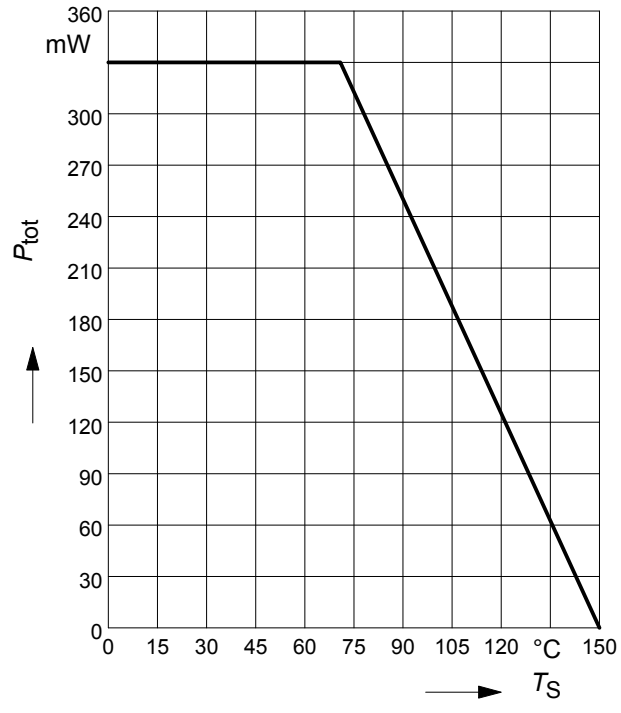
Collector-base capacitance $C_{cb} = f(V_{CB})$

Emitter-base capacitance $C_{eb} = f(V_{EB})$



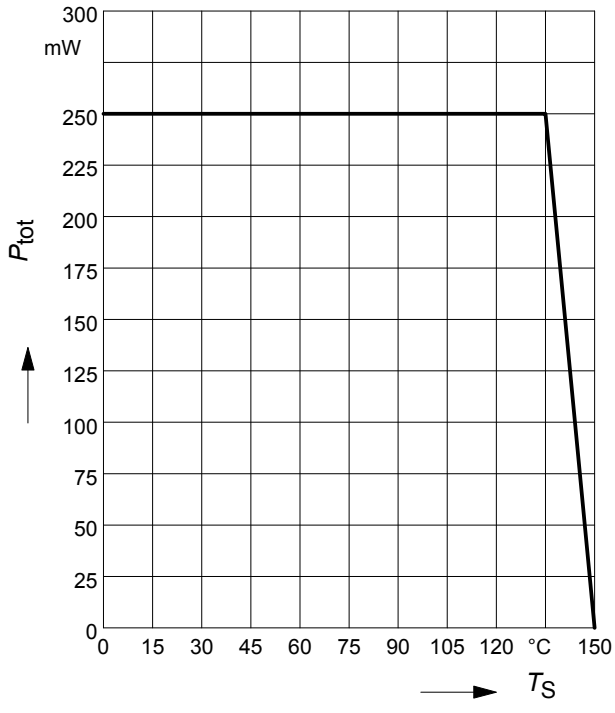
Total power dissipation $P_{tot} = f(T_S)$

BC856-BC860



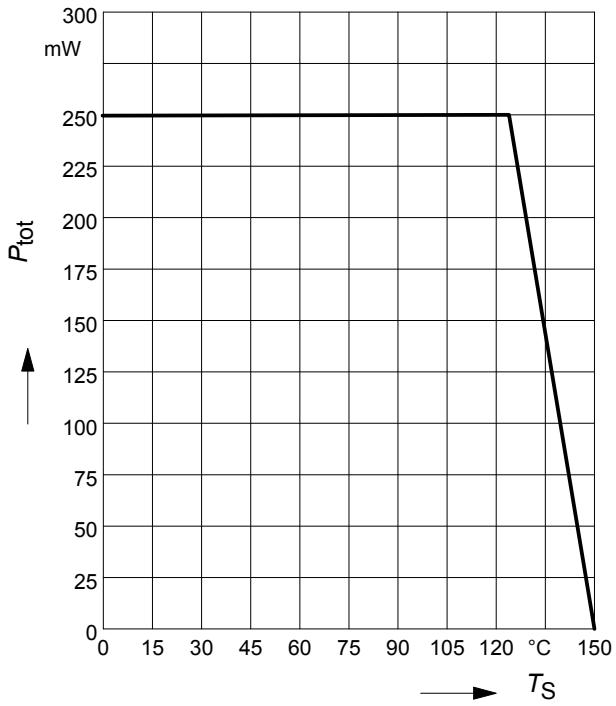
Total power dissipation $P_{tot} = f(T_S)$

BC857BL3



Total power dissipation $P_{tot} = f(T_S)$

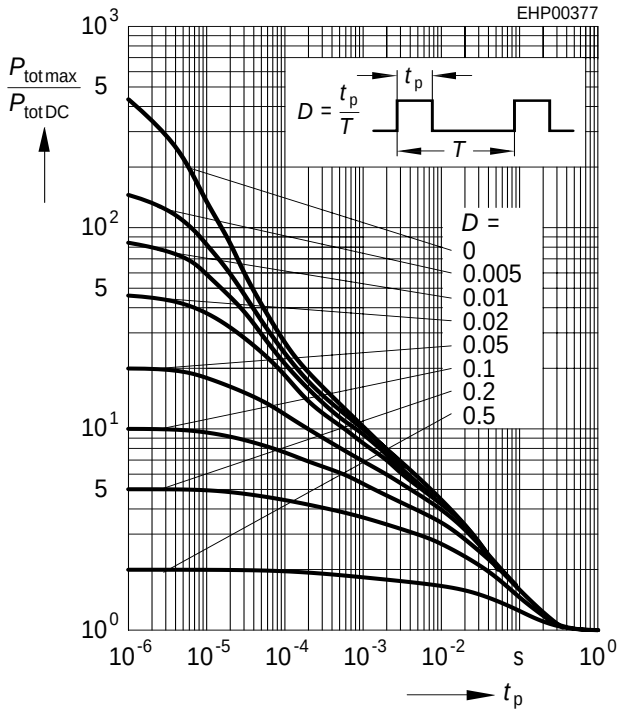
BC857W-BC860W



Permissible Pulse Load

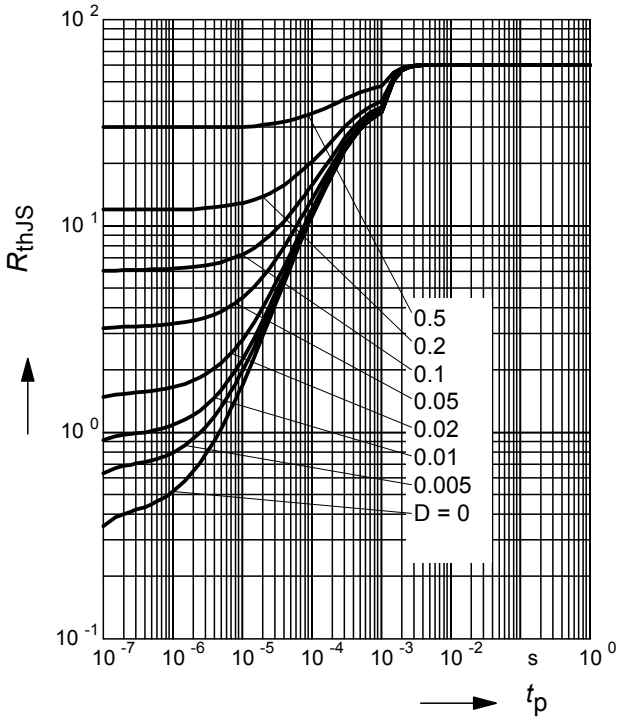
$P_{totmax}/P_{totDC} = f(t_p)$

BC857/W-BC860/W



Permissible Puls Load $R_{thJS} = f(t_p)$

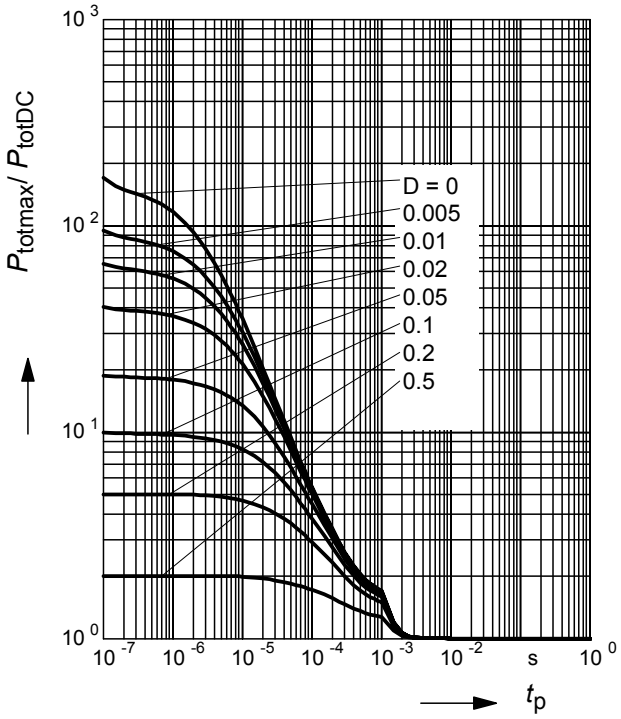
BC857BL3



Permissible Pulse Load

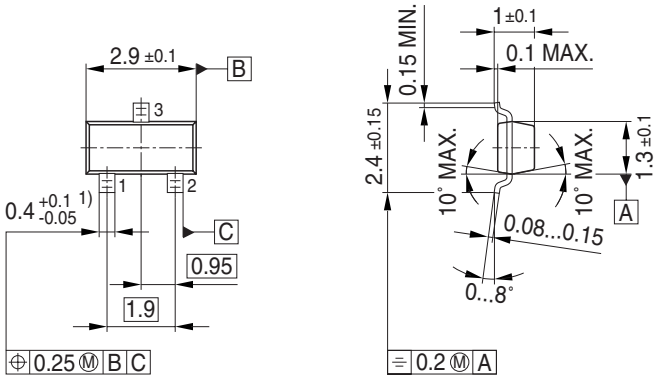
$P_{totmax}/P_{totDC} = f(t_p)$

BC857BL3



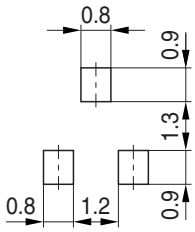
Package Outline



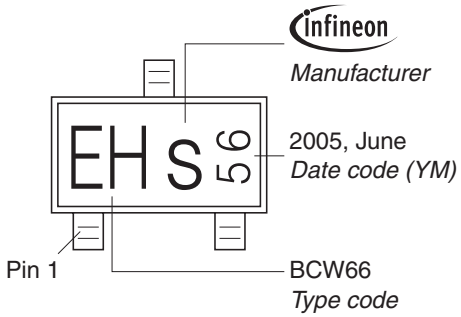


1) Lead width can be 0.6 max. in dambar area

Foot Print

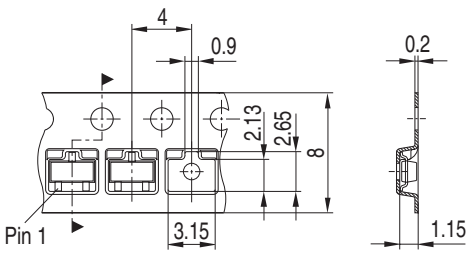


Marking Layout (Example)



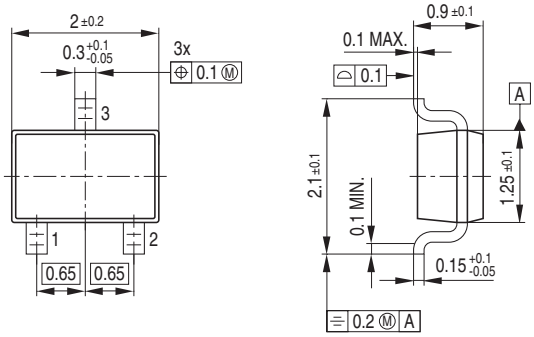
Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel

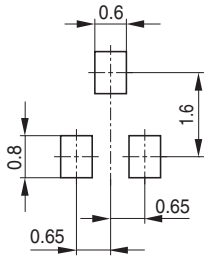


Package Outline

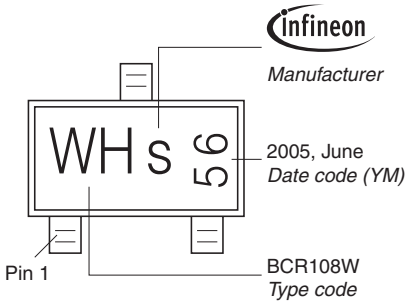




Foot Print

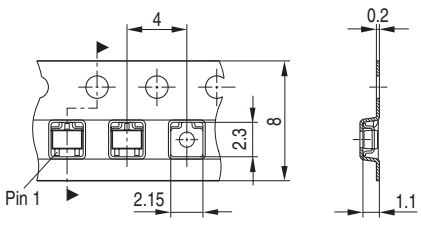


Marking Layout (Example)

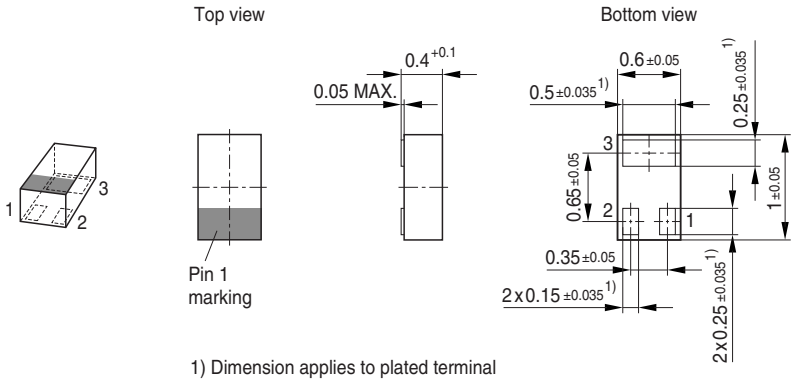


Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



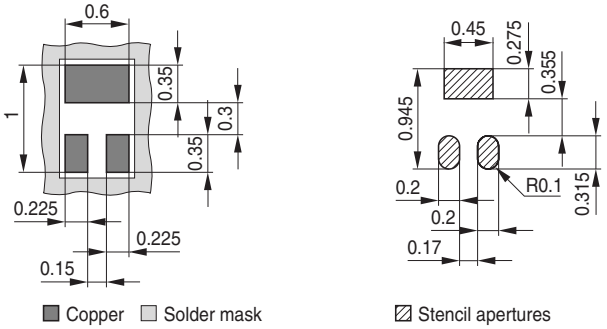
Package Outline



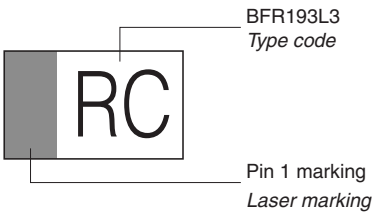
1) Dimension applies to plated terminal

Foot Print

For board assembly information please refer to Infineon website "Packages"

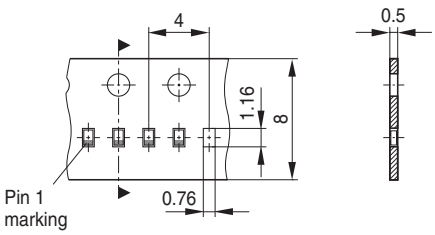


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel



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